

TO-92L Plastic-Encapsulate Transistors

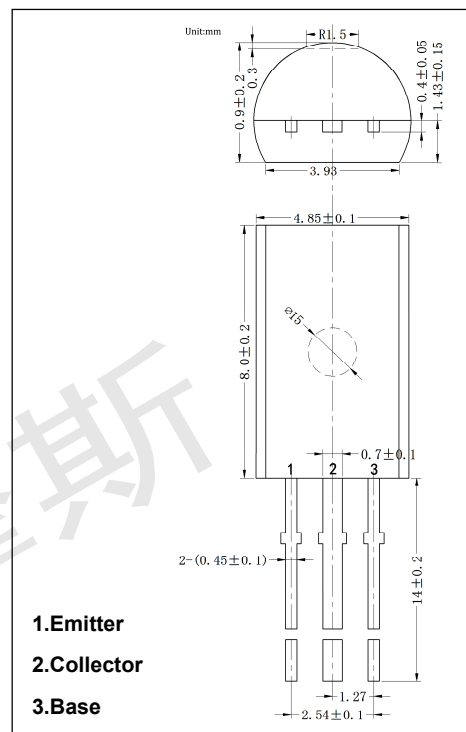
Features

- Low Saturation Voltage: $V_{CE(sat)}=0.5V(Max)(I_C=1A)$
- High Speed Switching Time: $t_{stg}=1\mu s(Typ.)$
- Complementary to 2SA1020

Marking: C2655Y3AL

Maximum Ratings ($T_a=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector Base Voltage	50	V
V_{CEO}	Collector Emitter Voltage	50	V
V_{EBO}	Emitter Base Voltage	5	V
I_C	Collector Current	1.5	A
P_C	Collector Power Dissipation	900	mW
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	- 55 to +150	$^{\circ}C$



Electrical Characteristics ($T_a=25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=100\mu A, I_E=0$	50			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA, I_B=0$	50			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=100\mu A, I_C=0$	5			V
I_{CBO}	Collector cut-off current	$V_{CB}=50V, I_E=0$			1	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V, I_C=0$			1	μA
$h_{FE(1)}$	DC current gain	$V_{CE}=5V, I_C=1mA$	200		300	
$h_{FE(2)}$		$V_{CE}=5V, I_C=10mA$	70			
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=1A, I_B=50mA$			0.5	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C=1A, I_B=50mA$			1.2	V
f_T	Transition frequency	$V_{CE}=2V, I_C=500mA$		100		MHz
C_{ob}	Collector output capacitance	$V_{CB}=10V, I_E=0, f=1MHz$		30		pF
t_{on}	Turn-on time	$V_{CC}=30V, I_{B1}=-I_{B2}=0.05A, I_C=1A$		0.15		μs
t_s	Storage time			2		μs
t_f	Fall time			0.15		μs



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NPN Transistors



Typical Characteristics

